

## UNITED S. ES DEPARTMENT OF COMMERCI Patent and Trademark Office

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APPLICATION NUMBER FILING DATE FIRST NAMED APPLICANT ATTORNEY DOCKET NO.

10/046, 346

EXAMINER

G. MUNSON'

ARTUNIT PAPER NUMBER

14

•	DATE MAILED:
INTERVIEW SUMMARY	
All participants (applicant, applicant's representative, PTO pe	ersonnel):
1) B. JOHNSON	(3)
(2)	(4)
Date of Interview 2 March 200 4	(4)
	nal (copy is given to applicant applicant's representative).
	If yes, brief description:
Agreement  was reached.  was not reached.	
Claim(s) discussed: 1, 7	
Identification of prior art discussed: Suzuki, Ea	dmond etal, Hermansson
·	
Description of the general nature of what was agreed to if a	an agreement was reached, or any other comments: Discussed case
and possible distinctions	over the references.
and possibile disconnection	
( A fuller description, if necessary, and a copy of the amendmust be attached. Also, where no copy of the amendments attached.)	dments, if available, which the examiner agreed would render the claims allowable s which would render the claims allowable is available, a summary thereof must be
It is not necessary for applicant to provide a separate	
	to the contrary. A FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION E OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office NE MONTH FROM THIS INTERVIEW DATE TO FILE A STATEMENT OF THE

Examiner Note: You must sign this form unless it is an attachment to another form.

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GENE M. MUNSON EXAMINER GROUP ART UNIT 2834 5000.221

Serial No. 10/046,346

Proposed Claim:

A bipolar structure comprising:

a silicon carbide substrate;

an n<sup>+</sup> type epitaxially grown terminating layer on said substrate;

an  $n^-$  type voltage blocking region of silicon carbide on said  $n^+$  type terminating layer;

a p-type epitaxially grown terminating layer on said blocking region

wherein said  $n^+$  and p type terminating layers each have a respective **thickness** greater than the minority carrier diffusion length in said layers.